

Type	Hits	Ref	Search Text	DBs	Time Stamp
BRS	253	S1	analyzing near plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	1	S2	S1 and ((RF or radio\$frequency)same ignite)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	3008	S3	(702/182 or 702/183 or 702/189 or 702/190).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	1497	S4	(118/723e).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	523	S5	(156/345.24 or 156/345.25).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	3571	S6	(216/59-61 or 216/67).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	8337	S7	S3 or S4 or S5 or S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	4673	S8	S7 and plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	209	S9	S8 and (RF near signal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	181	S10	S9 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	85	S11	S10 and (etch near rate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	5	S12	S11 and (analyzing same plasma)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	2	S13	S12 and fourier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	5	S14	S11 and fourier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	254	S15	analyzing near plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	3016	S17	(702/182 or 702/183 or 702/189 or 702/190).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	1497	S18	(118/723e).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	524	S19	(156/345.24 or 156/345.25).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	3573	S20	(216/59-61 or 216/67).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	8347	S21	S17 or S18 or S19 or S20	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	4675	S22	S21 and plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	210	S23	S22 and (RF near signal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	182	S24	S23 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	1	S16	S15 and ((RF or radio\$frequency)same ignite)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	85	S25	S24 and (etch near rate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	5	S26	S25 and (analyzing same plasma)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	2	S27	S26 and fourier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	5	S28	S25 and fourier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	254	S29	analyzing near plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	3016	S31	(702/182 or 702/183 or 702/189 or 702/190).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	1497	S32	(118/723e).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	524	S33	(156/345.24 or 156/345.25).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	3573	S34	(216/59-61 or 216/67).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	8347	S35	S31 or S32 or S33 or S34	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	4675	S36	S35 and plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	210	S37	S36 and (RF near signal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	182	S38	S37 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	254	S43	analyzing near plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	3016	S44	(702/182 or 702/183 or 702/189 or 702/190).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	1497	S45	(118/723e).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	524	S46	(156/345.24 or 156/345.25).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	3573	S47	(216/59-61 or 216/67).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	8347	S48	S44 or S45 or S46 or S47	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	4675	S49	S48 and plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	210	S50	S49 and (RF near signal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	182	S51	S50 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	1	S30	S29 and ((RF or radio\$frequency)same ignite)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	1	S52	S43 and ((RF or radio\$frequency)same ignite)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	85	S39	S38 and (etch near rate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	5	S40	S39 and (analyzing same plasma)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	2	S41	S40 and fourier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	5	S42	S39 and fourier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	85	S53	S51 and (etch near rate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	5	S54	S53 and (analyzing same plasma)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	2	S55	S54 and fourier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	5	S56	S53 and fourier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	89	S57	plot\$4 near etch near rate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	1	S58	S57 and (rf near signal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	1	S59	S57 and (rf same signal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	49	S60	S57 and (rf)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	2	S61	S60 and integrating	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	3569	S62	(438/738-751).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	532	S63	S62 and rf	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	0	S64	S63 and (integrat\$3 near plot\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	1	S65	S63 and (integrat\$3 same plot\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06
BRS	5	S66	I49 and ((calculate or determine)same etch\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	7/20/06